

AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) An in-plane switching mode liquid crystal display device, comprising:

first and second substrates;

a gate line and a data line arranged along first and second directions on the first substrate to define a pixel area;

a passivation layer on the first substrate except within the pixel area;

a light blocking system on the first substrate and ~~[[on]]~~ under a stepped portion of the passivation layer adjacent to the data line;

a plurality of common electrodes disposed within the pixel area, at least one of the common electrodes overlap a portion of the data line; and

a plurality of pixel electrodes disposed within the pixel area,

wherein the pixel electrodes and the common electrodes form a lateral electric field.

2. (Original) The device according to claim 1, further comprising a thin film transistor at a cross portion of the gate and data lines.

3. (Original) The device according to claim 1, wherein the thin film transistor includes:

a gate electrode on the first substrate;

a gate insulating layer on the gate electrode;

a semiconductor layer on the gate insulating layer;

an ohmic contact layer on the semiconductor layer; and

source and drain electrodes on the ohmic contact layer.

4. (Original) The device according to claim 3, wherein the gate insulating layer is formed along an entire surface of the first substrate.

5. (Original) The device according to claim 1, wherein the common electrodes and the pixel electrodes are formed on a common plane.

6. (Original) The device according to claim 5, wherein the common electrodes and the pixel electrodes are formed on the gate insulating layer.

7. (Original) The device according to claim 1, wherein the common electrodes include transparent conductive material.

8. (Original) The device according to claim 7, wherein the transparent conductive material includes at least one of indium tin oxide (ITO) and indium zinc oxide (IZO).

9. (Original) The device according to claim 1, wherein the light blocking system is formed with the gate electrode.

10. (Original) The device according to claim 1, wherein the passivation includes at least an organic material.

11. (Original) The device according to claim 10, wherein the organic material includes at least one of benzocyclobutene and photoacryl.

12. (Withdrawn) A method of fabricating an in-plane switching mode liquid crystal display device, comprising:

- forming a gate line and a light blocking line on a first substrate;
- forming a data line on the first substrate to define a pixel area;
- forming a plurality of pixel electrodes within the pixel area to be parallel with the data line;
- forming an organic layer along an entire surface of the first substrate;
- exposing the pixel electrodes by removing a portion of the organic layer; and
- forming a plurality of common electrodes on the first substrate, wherein at least one of the common electrodes along an outer portion of the pixel area overlap the data line.

13. (Withdrawn) The method according to claim 12, wherein the common electrodes include at least one of ITO and IZO.

14. (Currently Amended) A method of fabricating an in-plane switching mode liquid crystal display device, comprising:

- forming a gate line and a data line along first and second directions on a first substrate to define a pixel area;
- forming a passivation layer on the first substrate except within the pixel area;
- forming a light blocking system on the first substrate and under a stepped portion of the passivation layer adjacent to the data line;
- forming a plurality of common electrodes disposed within the pixel area, at least one of the common electrodes overlap a portion of the data line; and

forming a plurality of pixel electrodes disposed within the pixel area,
wherein the pixel electrodes and the common electrodes form a lateral electric field.

15. (Original) The method according to claim 14, further comprising forming a thin film transistor at a cross portion of the gate and data lines.

16. (Original) The method according to claim 14, wherein forming the thin film transistor includes:

- forming a gate electrode on the first substrate;
- forming a gate insulating layer on the gate electrode;
- forming a semiconductor layer on the gate insulating layer;
- forming an ohmic contact layer on the semiconductor layer; and
- forming source and drain electrodes on the ohmic contact layer.

17. (Original) The method according to claim 16, wherein the gate insulating layer is formed along an entire surface of the first substrate.

18. (Original) The method according to claim 14, wherein the common electrodes and the pixel electrodes are formed on a common plane.

19. (Original) The method according to claim 18, wherein the common electrodes and the pixel electrodes are formed on the gate insulating layer.

20. (Original) The method according to claim 14, wherein the common electrodes include transparent conductive material.

21. (Original) The method according to claim 20, wherein the transparent conductive material includes at least one of indium tin oxide (ITO) and indium zinc oxide (IZO).

22. (Original) The method according to claim 14, wherein the light blocking system and the gate electrode are simultaneously formed.

23. (Original) The method according to claim 14, wherein the passivation includes at least an organic material.

24. (Original) The method according to claim 23, wherein the organic material includes at least one of benzocyclobutene and photoacryl.

25. (Withdrawn) An in-plane switching mode liquid crystal display device, comprising:
a gate line and a light blocking line on a first substrate;
a data line on the first substrate to define a pixel area;
a plurality of pixel electrodes within the pixel area to be parallel with the data line;
an organic layer along an entire surface of the first substrate except for the pixel electrodes; and
a plurality of common electrodes on the first substrate,
wherein at least one of the common electrodes is provided along an outer portion of the pixel area to overlap the data line.

26. (Withdrawn) The device according to claim 25, wherein the common electrodes include at least one of ITO and IZO.